MOSFETs Silicon N-channel MOS (U-MOSIX-H)

# TPN7R006PL

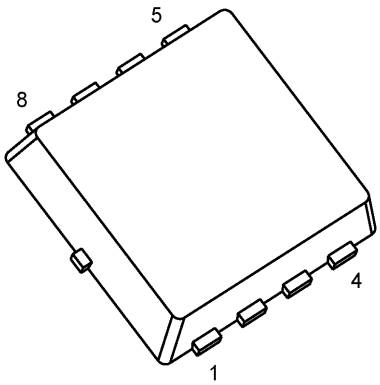
## 1. Applications

- High-Efficiency DC-DC Converters
- Switching Voltage Regulators

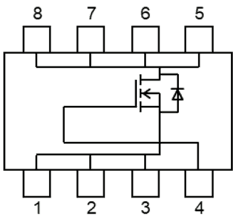
## 2. Features

(1) High-speed switching
(2) Small gate charge: $Q_{SW}$ = 6.8 nC (typ.)
(3) Small output charge: $Q_{oss}$ = 20 nC (typ.)
(4) Low drain-source on-resistance: $R_{DS(ON)}$ = 5.4 mΩ (typ.) ($V_{GS}$ = 10 V)
(5) Low leakage current: $I_{DSS}$ = 10 μA (max) ($V_{DS}$ = 60 V)
(6) Enhancement mode: $V_{th}$ = 1.5 to 2.5 V ($V_{DS}$ = 10 V, $I_D$ = 0.2 mA)

## 3. Packaging and Internal Circuit




TSON Advance




1, 2, 3: Source
4: Gate
5, 6, 7, 8: Drain

Start of commercial production
2016-12

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## 4. Absolute Maximum Ratings (Note) ($T_a$ = 25 °C unless otherwise specified)

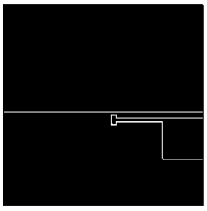
| Characteristics | | | Symbol | Rating | Unit |
|---|---|---|---|---|---|
| Drain-source voltage | | | $V_{DSS}$ | 60 | V |
| Gate-source voltage | | | $V_{GSS}$ | ±20 | |
| Drain current (DC) | ($T_c$ = 25 °C) | (Note 1), (Note 2) | $I_D$ | 54 | A |
| Drain current (DC) | (Silicon limit) | (Note 1), (Note 2) | | 76 | |
| Drain current (pulsed) | (t = 100 μs) | (Note 1) | $I_{DP}$ | 170 | |
| Power dissipation | ($T_c$ = 25 °C) | | $P_D$ | 75 | W |
| Power dissipation | | (Note 3) | | 2.67 | |
| Power dissipation | | (Note 4) | | 0.63 | |
| Single-pulse avalanche energy | | (Note 5) | $E_{AS}$ | 9.8 | mJ |
| Single-pulse avalanche current | | (Note 5) | $I_{AS}$ | 54 | A |
| Channel temperature | | | $T_{ch}$ | 175 | °C |
| Storage temperature | | | $T_{stg}$ | -55 to 175 | |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

## 5. Thermal Characteristics

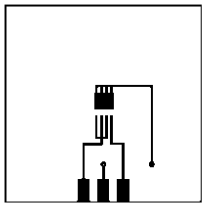
| Characteristics | | | Symbol | Max | Unit |
|---|---|---|---|---|---|
| Channel-to-case thermal resistance | ($T_c$ = 25 °C) | | $R_{th(ch-c)}$ | 2.0 | °C/W |
| Channel-to-ambient thermal resistance | ($T_a$ = 25 °C) | (Note 3) | $R_{th(ch-a)}$ | 56 | |
| Channel-to-ambient thermal resistance | ($T_a$ = 25 °C) | (Note 4) | | 235 | |

Note 1: Ensure that the channel temperature does not exceed 175 °C.
Note 2: Limited by silicon chip capability.
Note 3: Device mounted on a glass-epoxy board (a), Figure 5.1
Note 4: Device mounted on a glass-epoxy board (b), Figure 5.2
Note 5: $V_{DD}$ = 48 V, $T_{ch}$ = 25 °C (initial), L = 2.6 μH, $I_{AS}$ = 54 A



FR-4
25.4 × 25.4 × 1.6
(Unit: mm)
2 oz copper

**Fig. 5.1 Device Mounted on a Glass-Epoxy Board (a)**



FR-4
25.4 × 25.4 × 1.6
(Unit: mm)
2 oz copper

**Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)**

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



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# 6. Electrical Characteristics

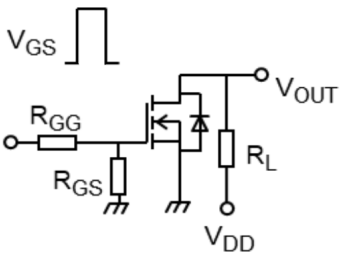
## 6.1. Static Characteristics ($T_a$ = 25 °C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Typ. | Max | Unit |
|---|---|---|---|---|---|---|
| Gate leakage current | $I_{GSS}$ | $V_{GS}$ = ±20 V, $V_{DS}$ = 0 V | — | — | ±0.1 | μA |
| Drain cut-off current | $I_{DSS}$ | $V_{DS}$ = 60 V, $V_{GS}$ = 0 V | — | — | 10 | |
| Drain-source breakdown voltage | $V_{(BR)DSS}$ | $I_D$ = 10 mA, $V_{GS}$ = 0 V | 60 | — | — | V |
| Drain-source breakdown voltage (Note 6) | $V_{(BR)DSX}$ | $I_D$ = 10 mA, $V_{GS}$ = -20 V | 45 | — | — | |
| Gate threshold voltage | $V_{th}$ | $V_{DS}$ = 10 V, $I_D$ = 0.2 mA | 1.5 | — | 2.5 | |
| Drain-source on-resistance | $R_{DS(ON)}$ | $V_{GS}$ = 4.5 V, $I_D$ = 10 A | — | 9.2 | 13.5 | mΩ |
| | | $V_{GS}$ = 10 V, $I_D$ = 27 A | — | 5.4 | 7.0 | |

Note 6: If a reverse bias is applied between gate and source, this device enters $V_{(BR)DSX}$ mode. Note that the drain-source breakdown voltage is lowered in this mode.

## 6.2. Dynamic Characteristics ($T_a$ = 25 °C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Typ. | Max | Unit |
|---|---|---|---|---|---|---|
| Input capacitance | $C_{iss}$ | $V_{DS}$ = 30 V, $V_{GS}$ = 0 V, f = 1 MHz | — | 1440 | 1875 | pF |
| Reverse transfer capacitance | $C_{rss}$ | | — | 35 | 70 | |
| Output capacitance | $C_{oss}$ | | — | 300 | — | |
| Gate resistance | $r_g$ | — | — | 0.8 | 1.3 | Ω |
| Switching time (rise time) | $t_r$ | See Fig. 6.2.1 | — | 3.6 | — | ns |
| Switching time (turn-on time) | $t_{on}$ | | — | 11 | — | |
| Switching time (fall time) | $t_f$ | | — | 3.9 | — | |
| Switching time (turn-off time) | $t_{off}$ | | — | 21 | — | |




$V_{DD}$ ≈ 30 V
$V_{GS}$ = 0 V/ 10 V
$I_D$ = 27 A
$R_L$ = 1.1 Ω
$R_{GG}$ = 4.7 Ω
$R_{GS}$ = 4.7 Ω
Duty ≤ 1 %, $t_w$ = 10 μs

**Fig. 6.2.1 Switching Time Test Circuit**

## 6.3. Gate Charge Characteristics ($T_a$ = 25 °C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Typ. | Max | Unit |
|---|---|---|---|---|---|---|
| Total gate charge (gate-source plus gate-drain) | $Q_g$ | $V_{DD}$ ≈ 30 V, $V_{GS}$ = 10 V, $I_D$ = 27 A | — | 20 | — | nC |
| | | $V_{DD}$ ≈ 30 V, $V_{GS}$ = 4.5 V, $I_D$ = 27 A | — | 9.8 | — | |
| Gate-source charge 1 | $Q_{gs1}$ | $V_{DD}$ ≈ 30 V, $V_{GS}$ = 10 V, $I_D$ = 27 A | — | 5.8 | — | |
| Gate-drain charge | $Q_{gd}$ | | — | 3.6 | — | |
| Gate switch charge | $Q_{SW}$ | | — | 6.8 | — | |
| Output charge | $Q_{oss}$ | $V_{DS}$ = 30 V, $V_{GS}$ = 0 V | — | 20 | — | |



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## 6.4. Source-Drain Characteristics ($T_a$ = 25 °C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Typ. | Max | Unit |
|---|---|---|---|---|---|---|
| Reverse drain current (pulsed) (Note 7) | $I_{DRP}$ (t = 100 μs) | — | — | — | 170 | A |
| Diode forward voltage | $V_{DSF}$ | $I_{DR}$ = 54 A, $V_{GS}$ = 0 V | — | — | -1.2 | V |
| Reverse recovery time | $t_{rr}$ | $V_R$ = 30 V, $I_{DR}$ = 13.5 A, $V_{GS}$ = 0 V, $-dI_{DR}/dt$ = 100 A/μs | — | 28 | — | ns |
| Reverse recovery charge | $Q_{rr}$ | | — | 22 | — | nC |

Note 7: Ensure that the channel temperature does not exceed 175 °C.

## 7. Marking

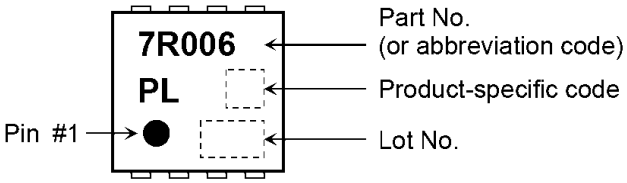


Fig. 7.1 Marking



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## 8. Characteristics Curves (Note)

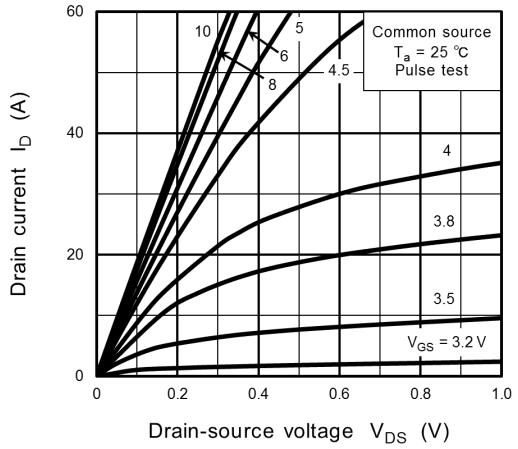


Fig. 8.1 $I_D$ - $V_{DS}$

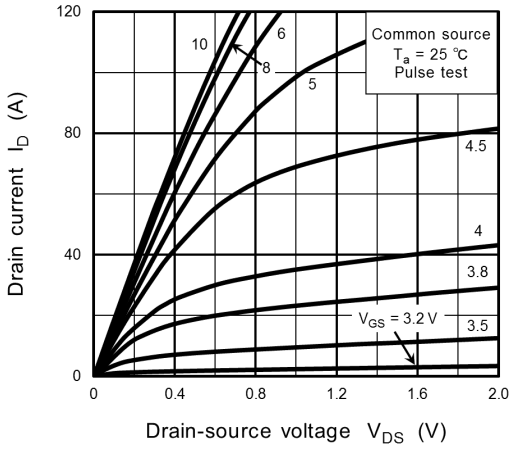


Fig. 8.2 $I_D$ - $V_{DS}$

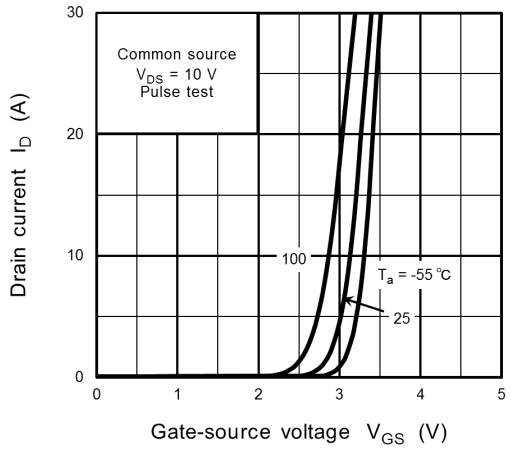


Fig. 8.3 $I_D$ - $V_{GS}$

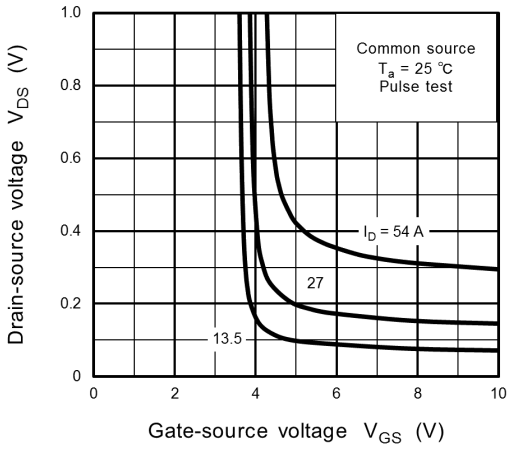


Fig. 8.4 $V_{DS}$ - $V_{GS}$

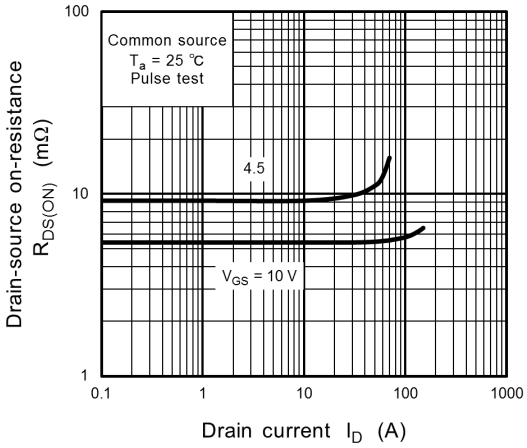


Fig. 8.5 $R_{DS(ON)}$ - $I_D$

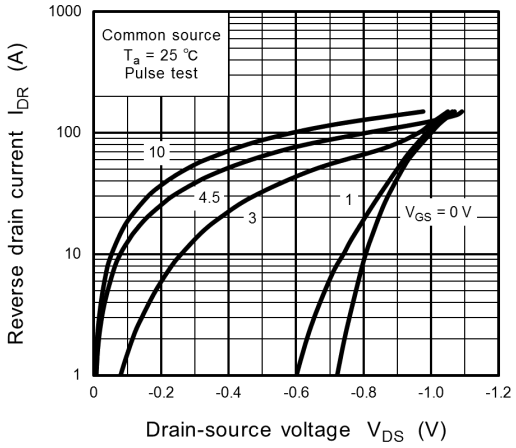


Fig. 8.6 $I_{DR}$ - $V_{DS}$



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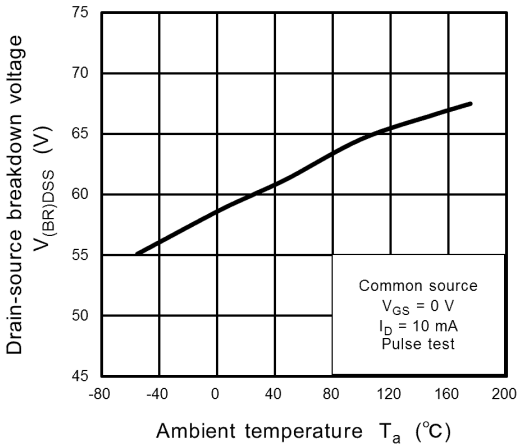


**Fig. 8.7 $V_{(BR)DSS}$ - $T_a$**

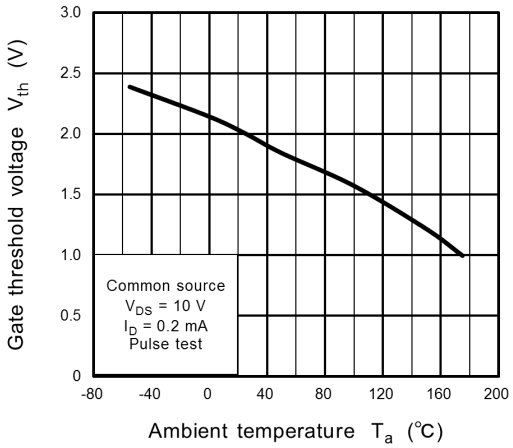


**Fig. 8.8 $V_{th}$ - $T_a$**

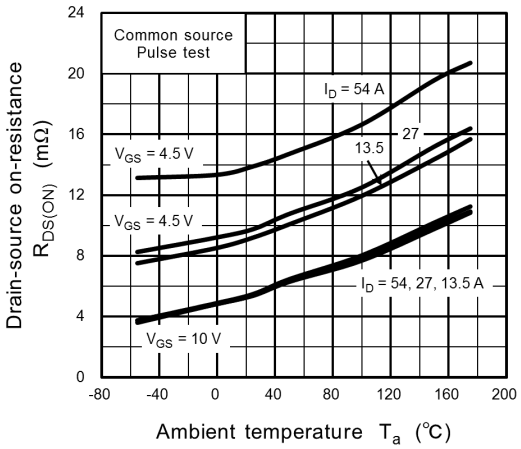


**Fig. 8.9 $R_{DS(ON)}$ - $T_a$**

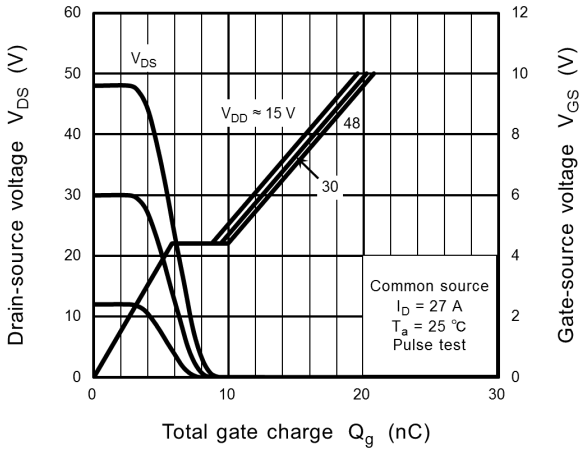


**Fig. 8.10 Dynamic Input/Output Characteristics**

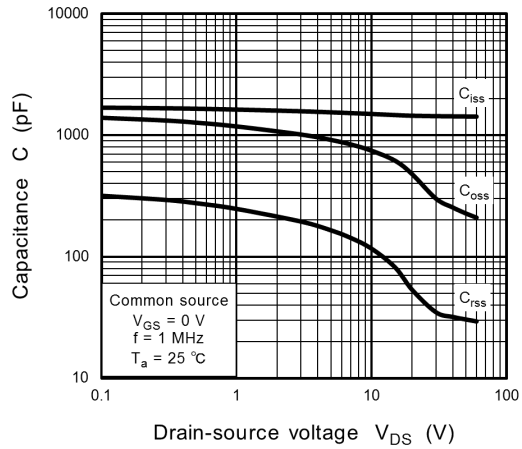


**Fig. 8.11 Capacitance - $V_{DS}$**

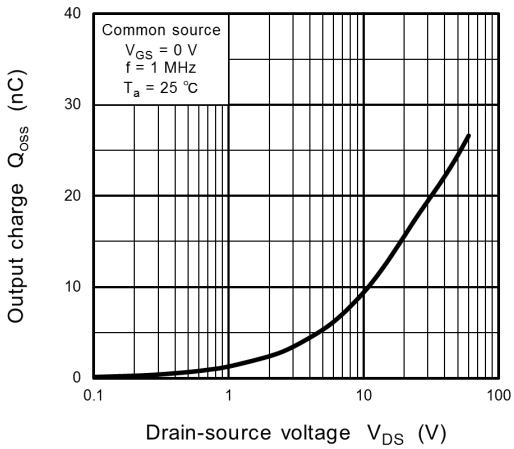


**Fig. 8.12 $Q_{oss}$ - $V_{DS}$**



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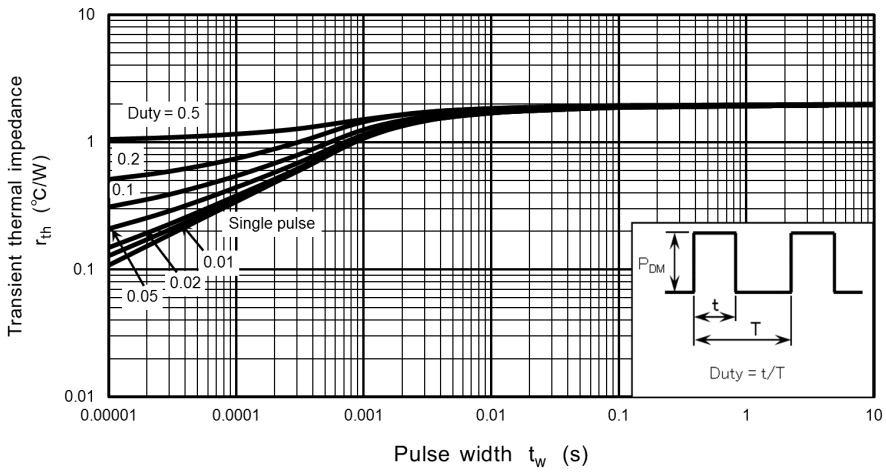


**Fig. 8.13 $r_{th}$ - $t_w$**
**(Guaranteed Maximum)**

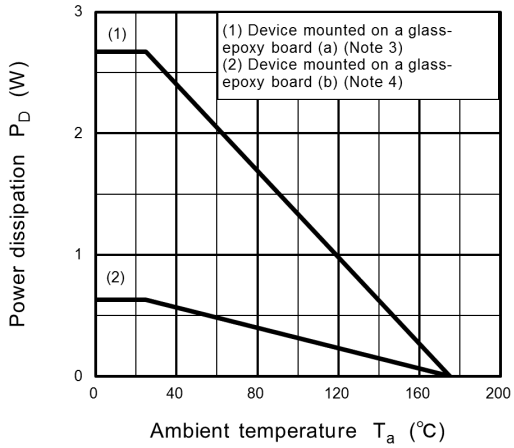


**Fig. 8.14 $P_D$ - $T_a$**
**(Guaranteed Maximum)**

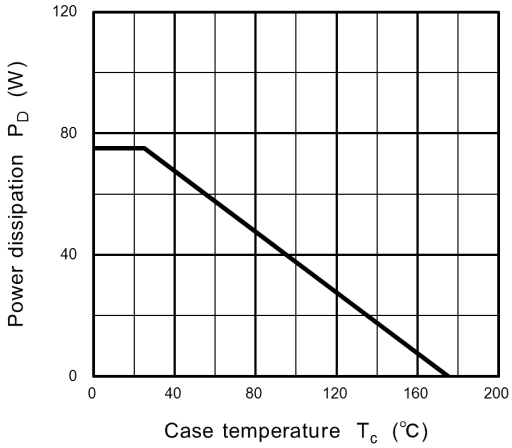


**Fig. 8.15 $P_D$ - $T_c$**
**(Guaranteed Maximum)**

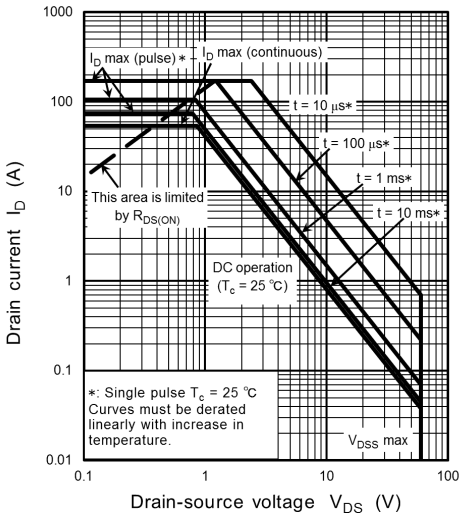


**Fig. 8.16 Safe Operating Area**
**(Guaranteed Maximum)**

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



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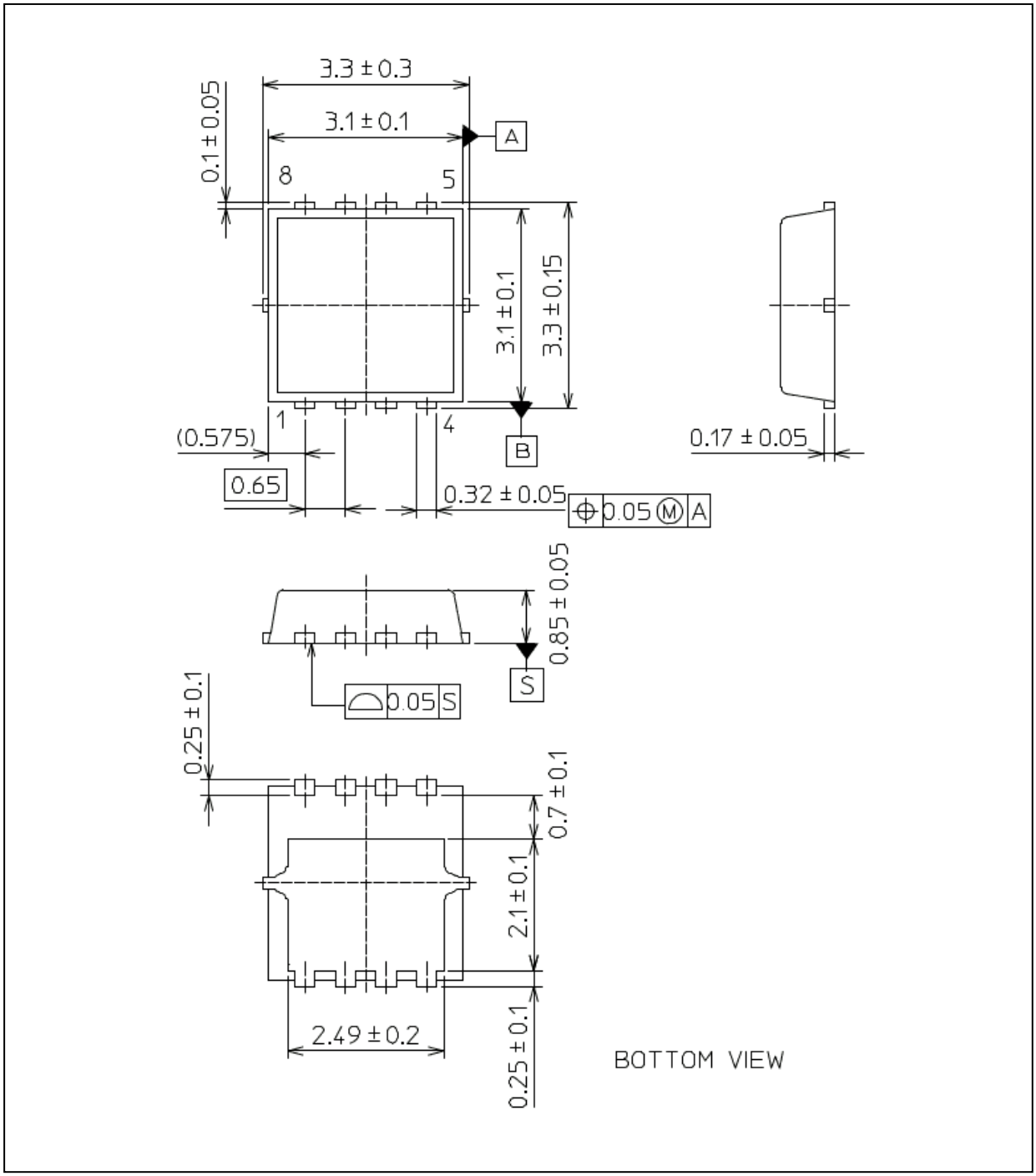
## Package Dimensions

Unit: mm




Weight: 0.026 g (typ.)

| Package Name(s) |
|---|
| TOSHIBA: 2-3X1S |
| Nickname: TSON Advance |



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